

June 2011

FAN4852 9MHz Low-Power Dual CMOS Amplifier

Features

- 0.8mA Supply Current
- 9 MHz Bandwidth
- Output Swing to within 10mV of Either Rail
- Input Voltage Range Exceeds the Rails
- 6V/µs Slew Rate
- 11nV/√Hz Input Voltage Noise
- Fully Specified at +3.3V and +5V Supplies

Applications

- Piezoelectric Sensors
- PCMCIA, USB
- Mobile Communications / Battery-Powered Devices
- Notebooks and PDAs
- Active Filters
- Signal Conditioning
- Portable Test Instruments.

Description

The FAN4852 is a dual, rail-to-rail output, low-power, CMOS amplifier that consumes only $800\mu A$ of supply current, while providing $\pm 50 \text{mA}$ of output short-circuit current. This amplifier is designed to operate supplies from 2.5V to 5V.

Additionally, the FAN4852 is EMI hardened, which minimizes EMI interference. It has a maximum input offset voltage of 1mV and an input common-mode range that includes ground.

The FAN4852 is designed on a CMOS process and provides 9MHz of bandwidth and 6V/µs of slew rate. The combination of low-power, low-voltage operation and a small package make this amplifier well suited for general-purpose and battery-powered applications.

Ordering Information

Part Number	Operating Temperature Range	Package	Packing Method	
FAN4852IMU8X	-40 to +85°C	8-Lead MSOP Package	3000 on Tape and Reel	

Pin Configuration

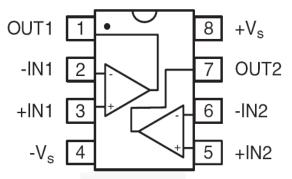


Figure 1. Pin Assignments

Pin Definitions

Pin#	Name	Description
1	OUT1	Output, Channel 1
2	-IN1	Negative Input, Channel 1
3	+IN1	Positive Input, Channel 1
4	-Vs	Negative Supply
5	+IN2	Positive Input, Channel 2
6	-IN2	Negative Input, Channel 2
7	OUT2	Output, Channel 2
8	+Vs	Positive Supply

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Functional operation under any of these conditions is NOT implied. Performance and reliability are guaranteed only if operating conditions are not exceeded.

Symbol	Parameter	Min.	Max.	Unit
Vcc	Supply Voltage	0	6	V
V_{IN}	Input Voltage Range	-V _S -0.5	+V _S +0.5	V
TJ	Junction Temperature		+150	°C
T _{STG}	Storage Temperature	-65	+150	°C
TL	Lead Soldering, 10 Seconds		+260	°C
Θ_{JA}	Thermal Resistance ⁽¹⁾		206	°C/W

Note:

1. Package thermal resistance JEDEC standard, multi-layer test boards, still air.

ESD Information

Symbol	Parameter	Min.	Тур.	Max.	Unit
ESD	Human Body Model, JESD22-A114		8		kV
ESD	Charged Device Model, JESD22-C101		2		KV

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter		Тур.	Max.	Unit
T_A	Operating Temperature Range	-40		+85	°C
Vs	Supply Voltage Range	2.5	3.3	5.0	V

Electrical Specifications at +3.3V

+V_S=+3.3V, -Vs = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
	0	T _A =25°C		0.8	1.0	^
Is	Supply Current ⁽²⁾	Full Temperature Range			1.1	- mA
		Sourcing $V_O=V_{CM}$, $V_{IN}=100 \text{mV}$, $T_A=25^{\circ}\text{C}$	25	50		
,	Short-Circuit Output Current ⁽²⁾	Sourcing V _O =V _{CM} , V _{IN} =100mV, Full Temperature Range	20			^
I _{sc}	isc Short-Girduk Output Guirent	Sinking $V_O=V_{CM}$, $V_{IN}=-100$ mV, $T_A=25$ °C	28	46		- mA
		Sinking V _O =V _{CM} , V _{IN} =-100mV, Full Temperature Range	20			
		V _{RFpeak} =100mVp, (-20dBVp) f=400MHz		75		
EMIRR	MIRR EMI Rejection Ratio, +IN and -IN ⁽⁴⁾	V _{RFpeak} =100mVp, (-20dBVp) f=900MHz		78		dB
		V _{RFpeak} =100mVp, (-20dBVp) f=1800MHz		87		
		2.7V≤V+≤3.3V, V _O =1V, T _A =25°C	75	95		
PSRR	R Power Supply Rejection Ratio ⁽²⁾	2.7V≤V+≤3.3V, V _O =1V, Full Temperature Range	74			dB
		-0.2V <v<sub>CM <v+-1.2v, t<sub="">A=25°C</v+-1.2v,></v<sub>	76	117		
CMRR	Common Mode Rejection Ratio ⁽²⁾	-0.2V <v<sub>CM <v+-1.2v, Full Temperature Range</v+-1.2v, </v<sub>	75			dB
CMIR	Input Common Mode Voltage Range ⁽²⁾	CMRR≥76dB	-0.2		2.1	V
Vos	Input Offset Voltage ⁽²⁾	T _A =25°C		±0.3	±1.0	mV
Vos	Input Offset Voltage	Full Temperature Range			±1.2	1110
$dV_{\text{IO}} \\$	Average Drift ⁽³⁾			±0.4	±2.0	μV/°C
los	Input Offset Current			1		pА
		T _A =				
I _{bn_Char}	Input Bias Current ⁽³⁾	T _A =25°C		0.1	10.0	pA
on_Char	input bias ourient	Full Temperature Range			500	PΛ
en	Input-Referred Voltage Noise	f=1kHz		11		nV/√Hz
on	Input Notoriou voltage (voice	f=10kHz		10		11 0 / 11 12
İn	Input-Referred Current Noise	f=1kHz		0.005		pA/√Hz

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Electrical Specifications at +3.3V

+V_S=+3.3V, -Vs = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
		R_L =2k Ω to V+/2, T_A =25°C		21	35	
	Output Voltage Swing High ⁽²⁾	R _L =2kΩ to V+/2, Full Temperature Range			43	
	$V_O = (+V_S) - V_{OUT}$	R _L =10kΩ to V+/2, T _A =25°C		4	10	mV
V		R_L =10k Ω to V+/2, Full Temperature Range			12	
Vo		R_L =2k Ω to V+/2, T_A =25°C		20	32	
	Output Voltage Swing Low ⁽²⁾	R_L =2k Ω to V+/2, Full Temperature Range			43	mV
	$V_O = V_{OUT} + (-V_S)$	R _L =10kΩ to V+/2, T _A =25°C		3	11	IIIV
		R _L =10kΩ to V+/2, Full Temperature Range			14	
GBW	Gain Bandwidth Product		\	9		MHz
		R_L =2k Ω , V_O =0.15 to 1.65V, V_O =3.15 to 1.65V, T_A =25°C	100	114		
	(3)	R_L =2k Ω , V_O =0.15 to 1.65V, V_O =3.15 to 1.65V, Full Temperature Range	97			
A _{VOL}	Large Signal Voltage Gain ⁽³⁾	R_L =10k Ω , V_O =0.1 to 1.65V, V_O =3.2 to 1.65V, T_A =25°C	100	115		dB
		R_L =10k Ω , V_O =0.1 to 1.65V, V_O =3.2 to 1.65V, Full Temperature Range	97			
Rout	Closed-Loop Impedance	f=6MHz		6		Ω
R _{IN}	Input Resistance			10		GΩ
C _{IN}	Input Capacitance	Common Mode		11		pF
OIN	input Gapacitanice	Differential Mode		6		
Фм	Phase Margin			86		۰
SR	Slew Rate	Av=+1, V _O =1V _{pp} 10%-90%		6.1		V/µs
THD+N	Total Harmonic Distortion + Noise	f=1kHz, Av=1, BW=>500kHz		0.006		%

Notes:

- 100% tested at T_A=25°C.
- Guaranteed by characterization. EMI rejection ratio is defined as EMIRR 20log (V_{RFpeak} / ΔV_{OS}).

Electrical Specifications at +5V

+V_S=+5V, -V_S = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
	0	T _A =25°C		0.9	1.1	4
Is	Supply Current ⁽⁵⁾	Full Temperature Range			1.2	- mA
		Sourcing $V_O=V_{CM}$, $V_{IN}=100 mV$, $T_A=25$ °C	60	90		
ı	Short-Circuit Output Current ⁽⁵⁾	Sourcing V _O =V _{CM} , V _{IN} =100mV, Full Temperature Range	48			A
I _{SC}	Short-Circuit Output Current	Sinking $V_O=V_{CM}$, $V_{IN}=-100$ mV, $T_A=25$ °C	58	90		- mA
		Sinking V _O =V _{CM} , V _{IN} =-100mV, Full Temperature Range	44			
	EMIRR EMI Rejection Ratio, +IN and -IN ⁽⁷⁾	V _{RFpeak} =100mVp, (-20dBVp) f=400MHz		75		
EMIRR		V _{RFpeak} =100mVp, (-20dBVp) f=900MHz		78		dB
		V _{RFpeak} =100mVp, (-20dBVp) f=1800MHz		87		
		2.7V≤V+≤5.5V, Vo=1V, T _A =25°C	75	105		
PSRR	Power Supply Rejection Ratio ⁽⁵⁾	2.7V≤V+≤5.5V, Vo=1V, Full Temperature Range	74			dB
CMRR	Common Mode Rejection Ratio ⁽⁵⁾	-0.2V≤V _{CM} ≤V+-1.2V	77	122		dB
CMIR	Input Common Mode Voltage Range ⁽⁵⁾	CMRR≥77dB	-0.2		3.8	V
\/	Input Offset Voltage ⁽⁵⁾	T _A =25°C		±0.3	±1.0	mV
Vos		Full Temperature Range			±1.2	IIIV
$dV_{\text{IO}} \\$	Average Drift ⁽⁶⁾			±0.4	±2.0	μV/°C
Ios	Input Offset Current			1		pA
		T _A =				
l. a.	Input Bias Current ⁽⁶⁾	T _A =25°C		0.1	10.0	- pA
I _{bn_Char}	Input bias Current	Full Temperature Range			500	PΛ
	Input-Referred Voltage Noise	f=1kHz		11		nV/√Hz
e _n	Imput-ixeleffed voltage Moise	f=10kHz		10		nV/√Hz
İn	Input-Referred Current Noise	f=1kHz		0.005		pA/√Hz

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Electrical Specifications at +5V

+V_S=+5V, -V_S = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
		R _L =2k Ω to V+/2, T _A =25°C		25	39	
	Output Voltage Swing High ⁽⁵⁾	R_L =2k Ω to V+/2, Full Temperature Range			47	
	Output voitage Swing High	R _L =10k Ω to V+/2, T _A =25°C		4	11	mV
V		R_L =10k Ω to V+/2, Full Temperature Range			13	
Vo		R _L =2k Ω to V+/2, T _A =25°C		24	38	
	Output Voltage Swing Low ⁽⁵⁾	R_L =2k Ω to V+/2, Full Temperature Range			50	mV
	Output voitage Swing Low	R _L =10k Ω to V+/2, T _A =25°C		3	15	mv
		R _L =10kΩ to V+/2, Full Temperature Range			1	
GBW	Gain Bandwidth Product		\	9		MHz
		R_L =2k Ω , V_O =0.15 to 2.5V, V_O =4.85 to 2.5V, T_A =25°C	105	118		
	(6)	R_L =2k Ω , V_O =0.15 to 2.5V, V_O =4.85 to 2.5V, Full Temperature Range	102			
A _{VOL}	Large Signal Voltage Gain ⁽⁶⁾	R_L =10kΩ, V_O =0.1 to 2.5V, V_O =4.9 to 2.5V, T_A =25°C	105	120		dB
		R_L =10k Ω , V_O =0.1 to 2.5V, V_O =4.9 to 2.5V, Full Temperature Range	102			
Rout	Closed-Loop Impedance	f=6MHz		6		Ω
R _{IN}	Input Resistance			10		GΩ
C _{IN}	Input Capacitance	Common Mode		11		pF
OIN	input Gapacitanice	Differential Mode		6		
Фм	Phase Margin			94		۰
SR	Slew Rate	Av=+1, V _O =1V _{pp} 10%-90%	- //	6.2	,=/	V/µs
THD+N	Total Harmonic Distortion + Noise	f=1kHz, Av=1, BW=>500kHz		0.006		%

Notes:

- 100% tested at T_A=25°C.
- Guaranteed by characterization. EMI rejection ratio is defined as EMIRR 20log (V_{RFpeak} / ΔV_{OS}).

Typical Performance Characteristics

 $+V_S=+3.3V$, $-V_S=0V$, $V_{CM}=+V_S/2$, and $R_L=10K\Omega$ to $+V_S/2$, unless otherwise noted.

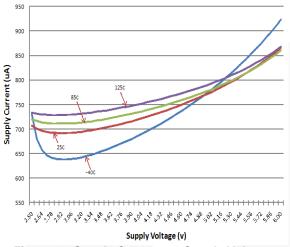
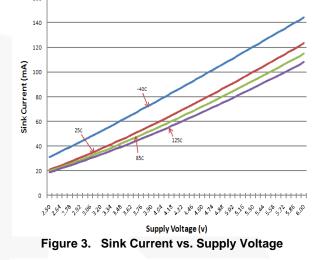


Figure 2. Supply Current vs. Supply Voltage



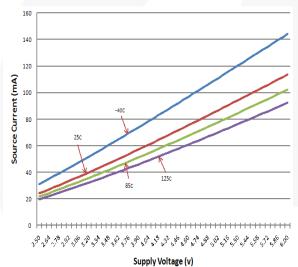


Figure 4. Source Current vs. Supply Voltage

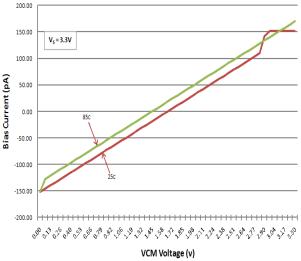
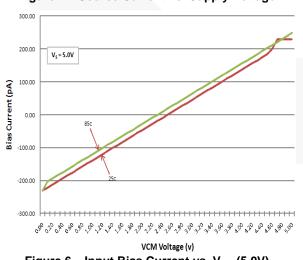


Figure 5. Input Bias Current vs. V_{CM} (3.3V)



Typical Performance Characteristics

+V_S=+3.3V, -V_S = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

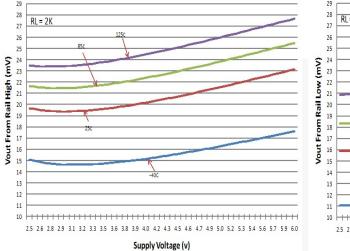
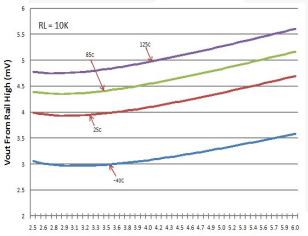
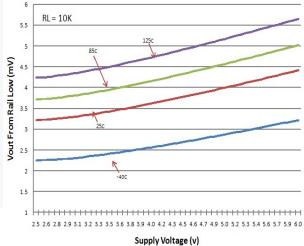


Figure 7. Output Swing High vs. Supply Voltage

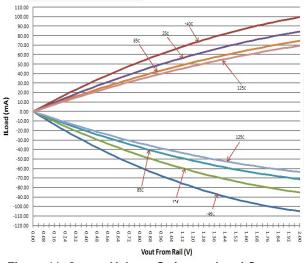
Supply Voltage (v)
Figure 8. Output Swing Low vs. Supply Voltage





Supply Voltage (v)
Figure 9. Output Swing High vs. Supply Voltage

Figure 10. Output Swing Low vs. Supply Voltage



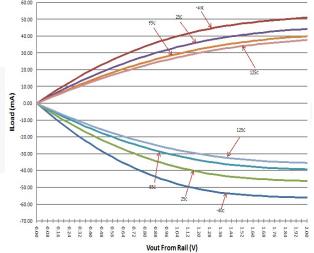


Figure 11. Output Voltage Swing vs. Load Current at 5.0V

Figure 12. Output Voltage Swing vs. Load Current at 3.3V

Typical Performance Characteristics +V_S=+3.3V, -V_S = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted. 100.0 100.0 PHASE PHASE 90.0 90.0 80.0 80.0 Gain (dB) Phase (Deg) Gain (dB) Phase (Deg) 70.0 70.0 60.0 60.0 GAIN-40TO 125 Deg C 50.0 50.0 40.0 40.0 100pF 30.0 30.0 20.0 20.0 10.0 10.0 0.0 -10.0 0.288 1.585 0.219 979.0 0.891 0.093 0.676 0.054 0.891 1.202 0.041 Frequency (MHz) Frequency (MHz) Figure 13. Open-Loop Gain/Phase vs. Temperature Figure 14. Open-Loop Gain/Phase vs. Load 80.0 -10.0 70.0 -20.0 -30.0 60.0 -40.0 Phase Margin (Deg) 3.3V -50.0 PSRR (dB) -60.0 50.0 PSRR 3.3V & 5.0V -70.0 -80.0 40.0 -90.0 -100.0 PSRR 3.3V & 5.0V 30.0 -110.0 -120.0 -130.0 -140.0 10.0 -150.0 -----Capactive Load (pF) Frequency (MHz) Figure 15. Phase Margin vs. Capacitive Load Figure 16. PSRR vs. Frequency 130.0 100.00 120.0 110.0 90.00 100.0 3.3 & 5.0V 80.00 90.0 CMRR (dB) 80.0 70.00 EMIRR (dB) 70.0 60.0 60.00 50.0 40.0 50.00 30.0 20.0 40.00 10.0

Frequency (MHz)

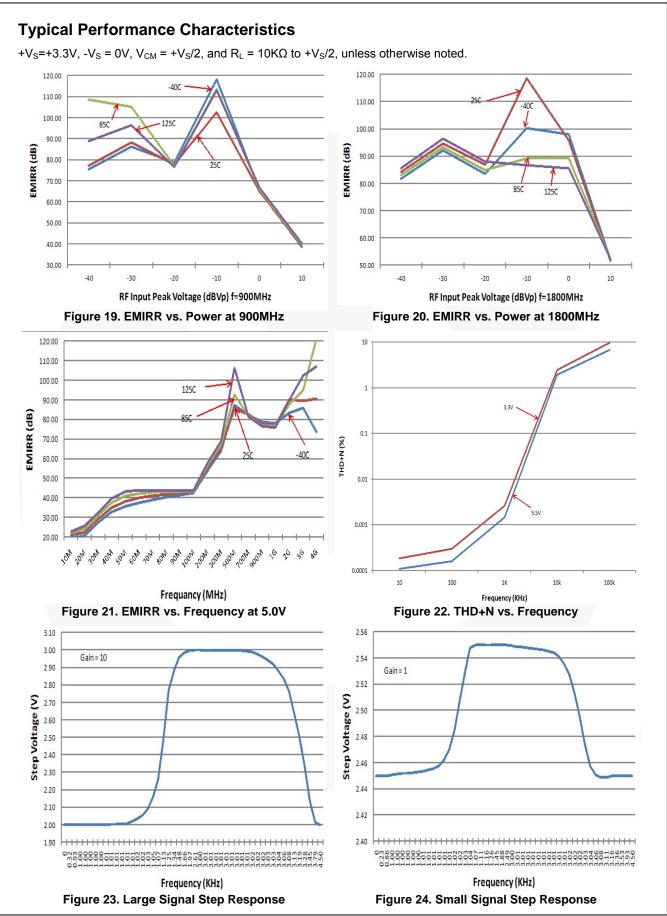
Figure 17. CMRR vs. Frequency

RF Input Peak Voltage (dBVp) f=400MHz

Figure 18. EMIRR vs. Power at 400MHz

30.00

20.00



Typical Performance Characteristics

+V_S=+3.3V, -V_S = 0V, V_{CM} = +V_S/2, and R_L = 10K Ω to +V_S/2, unless otherwise noted.

6.50 6.45

6.40

6.35

6.30

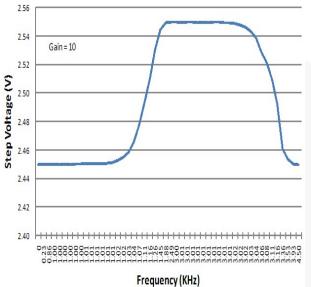
6.25

6.15

6.10

6.05

Slew Rate (V/uS)



Vcc (V)

Figure 25. Small Signal Step Response

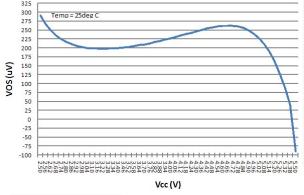
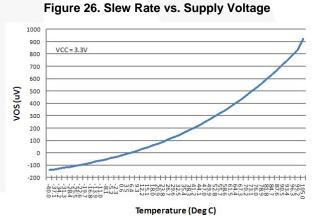


Figure 27. Vos vs. Supply Voltage



Application Information

General Description

The FAN4852 amplifier includes single-supply, generalpurpose amplifiers, fabricated on a CMOS process. The input and output are rail-to-rail and the part is unity gain stable. The typical non-inverting circuit schematic is shown in Figure 29.

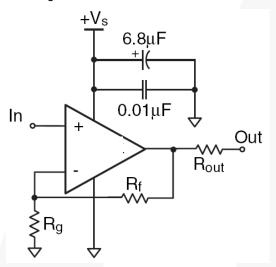


Figure 29. Typical Non-Inverting Configuration

Input Common Mode Voltage

The common mode input range includes ground. CMRR does not degrade when input levels are kept 1.2V below the rail. For the best CMRR when using a $V_{\rm S}$ of 5V, the maximum input voltage should 3.8V.

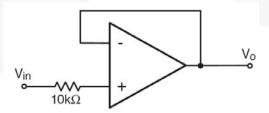


Figure 30. Circuit for Input Current Protection

Power Dissipation

The maximum internal power dissipation allowed is directly related to the maximum junction temperature. If the maximum junction temperature exceeds 150°C, performance degradation occurs. If the maximum junction temperature exceeds 150°C for an extended time, device failure may occur.

Overdrive Recovery

Overdrive of an amplifier occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the range is exceeded. The FAN4852 typically recovers in less than 500ns from an overdrive condition. Figure 31 shows the FAN4852 amplifier in an overdriven condition.

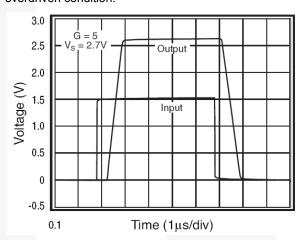


Figure 31. Overdrive Recovery

Driving Capacitive Loads

Figure 31 illustrates the response of the amplifier. A small series resistance ($R_{\rm S}$) at the output, illustrated in Figure 32, improves stability and settling performance. $R_{\rm S}$ values provided achieve maximum bandwidth with less than 2dB of peaking. For maximum flatness, use a larger $R_{\rm S}$. Capacitive loads larger than 500pF require the use of $R_{\rm S}$.

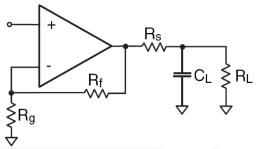


Figure 32. Typical Topology for Driving a Capacitive Load

Driving a capacitive load introduces phase-lag into the output signal, which reduces phase margin in the amplifier. The unity gain follower is the most sensitive configuration. In a unity gain follower configuration, the amplifier requires a 300Ω series resistor to drive a 100 pF load.

Layout Considerations

General layout and supply bypassing play major roles in high-frequency performance. Fairchild evaluation boards help guide high-frequency layout and aid in device testing and characterization. Follow the steps below as a basis for high-frequency layout:

- 1. Include 6.8μF and 0.01μF ceramic capacitors.
- Place the 6.8µF capacitor within 0.75 inches of the power pin.
- Place the 0.01µF capacitor within 0.1 inches of the power pin.
- Remove the ground plane under and around the part, especially near the input and output pins, to reduce parasitic capacitance.

Minimize all trace lengths to reduce series inductances.

Refer to the evaluation board layouts shown in Figure 33 for more information.

When evaluating only one channel, complete the following on the unused channel:

- 1. Ground the non-inverting input.
- 2. Short the output to the inverting input.

Evaluation Board	Description
FAN4852-010	Single Channel, Dual Supply

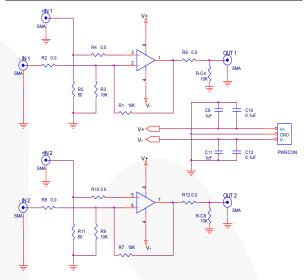


Figure 33. Evaluation Board Schematic

Physical Dimensions

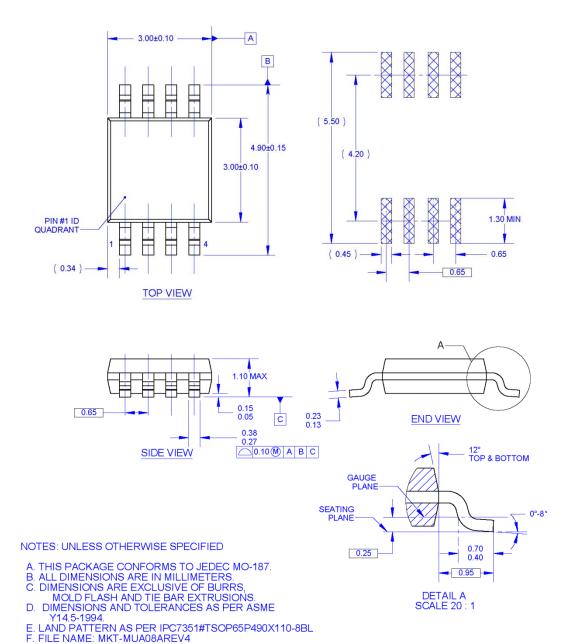


Figure 34. 8-Lead, Molded Small-Outline Package (MSOP)

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

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Gmax™ GTO™ IntelliMAX™ ISOPLANAR™

MegaBuck™ MICROCOUPLER" MicroFET™ MicroPak™ MicroPak2™

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Programmable Active Droop™ QFĔT

QS™ Quiet Series™ RapidConfigure™

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SignalWise™ SmartMax™ SMART START™ SPM®

STEALTH™ SuperFET⁶ SuperSOT™3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™ SYSTEM ... The Power Franchise®

The Right Technology for Your Success™

puwer.

TinyBoost™ TinyBuck™ TinyCalc™ TinyLogic⁶ TINYOPTO" TinyPower™ Tiný₽V⁄M™ TinyWire™ TranSiC[®] TriFault Detect™ TRUECURRENT®* μSerDes™

UHC Ultra FRFET™ UniFET™ VCXTM VisualMax™ XS™

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